

AMS-FOB

500mA 8.0kV 40nS

Ultra-Fast Recovery High Voltage Silicon Rectifier Diodes

INTRODUCE:

AMS high voltage silicon rectifier diode is made of high quality glass passivated chip and high reliability epoxy resin sealing structure.

FEATURES:

1. High reliability design.
2. High voltage, large current.
3. High frequency, Fast recovery.
4. Conform to RoHS and SGS.

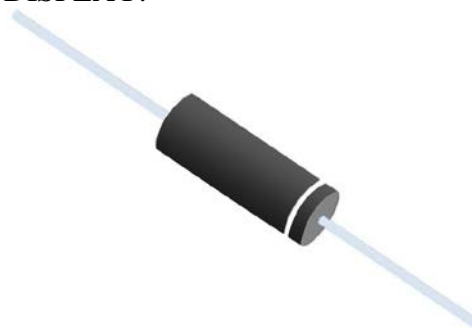
APPLICATIONS:

1. High voltage multiplier circuit
2. High frequency switching power supply
3. General purpose high voltage rectifier.
4. Laser power supply medical equipment

MECHANICAL DATA:

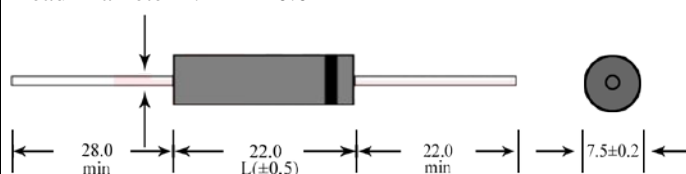
1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 2.55 grams (approx).

SHAPE DISPLAY:



SIZE: (Unit:mm) NAME: DO-722

Lead Diameter 1.2mm ±0.02



Unit:mm

MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Reverse Voltage	V_{RRM}	$T_A=25^{\circ}C$	8.0	kV
Non-Repetitive Peak Reverse Voltage	V_{RSM}	$T_A=25^{\circ}C$	--	kV
Average Forward Current Maximum	I_{FAVM}	$T_A=55^{\circ}C$	500	mA
		$T_{OIL}=55^{\circ}C$	--	mA
Non-Repetitive Forward Surge Current	I_{FSM}	$T_A=25^{\circ}C$; 50Hz Half-Sine Wave; 8.3mS	20	A
Junction Temperature	T_J		150	$^{\circ}C$
Allowable Operation Case Temperature	T_c		-40~+150	$^{\circ}C$
Storage Temperature	T_{STG}		-40~+150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS: $T_A=25^{\circ}C$ (Unless Otherwise Specified)

Items	Symbols	Condition	Data Value	Units
Maximum Forward Voltage Drop	V_{FM}	at $25^{\circ}C$; at I_{FAVM}	12	V
Maximum Reverse Current	I_{R1}	at $25^{\circ}C$; at V_{RRM}	0.5	μA
	I_{R2}	at $125^{\circ}C$; at V_{RRM}	50	μA
Maximum Reverse Recovery Time	T_{RR}	at $25^{\circ}C$; $I_F=0.5A$; $I_R=I_{FAVM}$; $I_{RR}=0.25mA$	40	nS
Junction Capacitance	C_J	at $25^{\circ}C$; $V_R=0V$; $f=1MHz$	7.5	pF

Tel. 1-973-377-9566 Fax. 1-973-377-3078

133 Kings Road
 Madison, New Jersey 07940
 United States of America

www.americanmicrosemi.com

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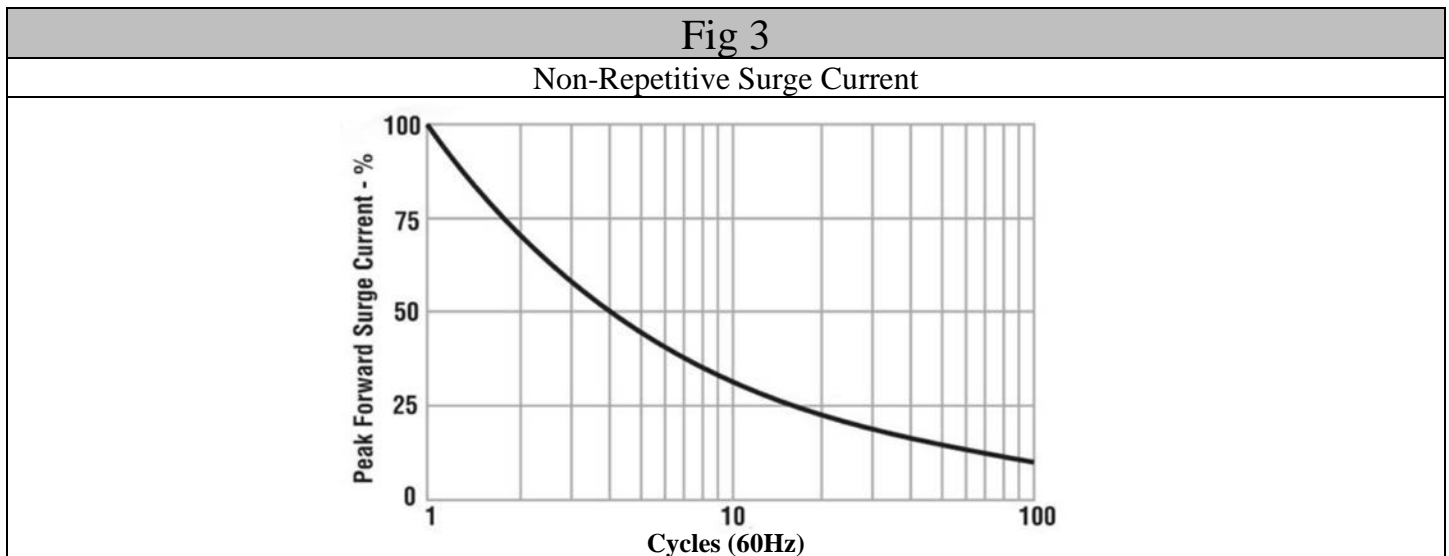
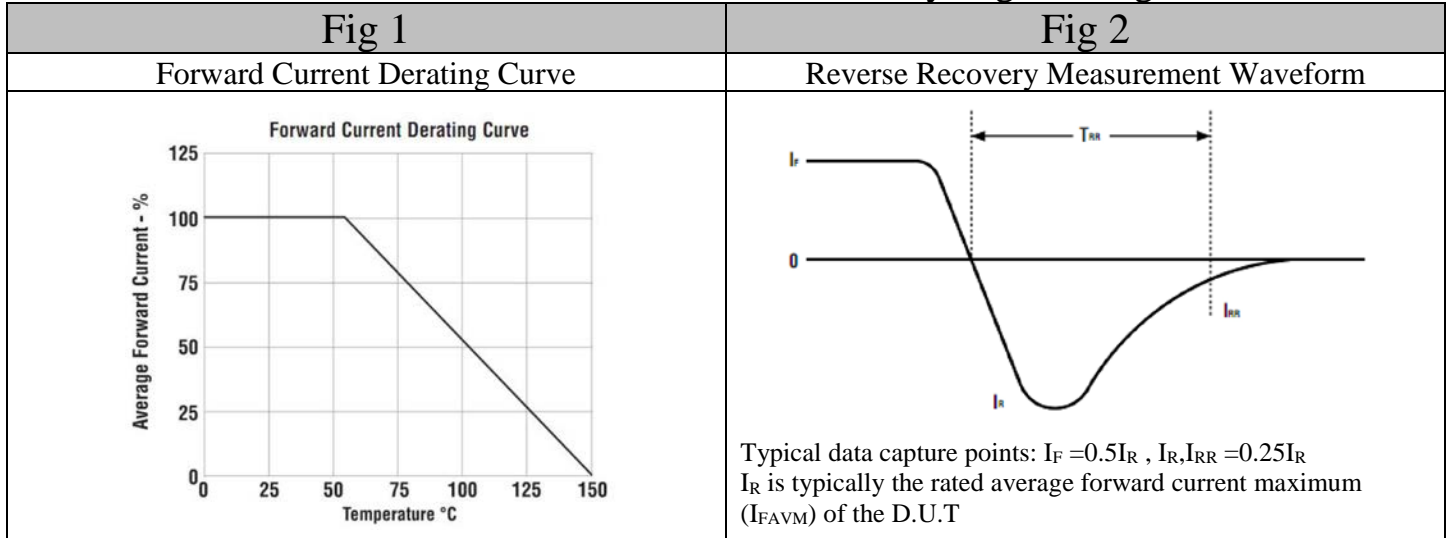
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DEKRA Certification Inc.
 AS9100C and ISO 9001:2008
 Certificate No. 131519.01



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 Ultra-Fast Recovery High Voltage Silicon Rectifier



	Type	Code	Cathode Mark
Marking			

Tel. 1-973-377-9566 Fax. 1-973-377-3078
 133 Kings Road
 Madison, New Jersey 07940
 United States of America

www.americanmicrosemi.com

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